# **SPICE Device Model SQ4401EY**



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# P-Channel 40 V (D-S) 175 °C MOSFET

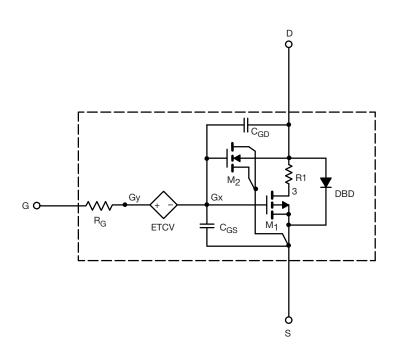
### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C<sub>gd</sub> model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### SUBCIRCUIT MODEL SCHEMATIC

### **CHARACTERISTICS**

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |                                                                               |                   |                  |      |
|------------------------------------------------------------------------|---------------------|-------------------------------------------------------------------------------|-------------------|------------------|------|
| PARAMETER                                                              | SYMBOL              | TEST CONDITIONS                                                               | SIMULATED<br>DATA | MEASURED<br>DATA | UNIT |
| Static                                                                 |                     |                                                                               |                   |                  |      |
| Gate-Source Threshold Voltage                                          | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$                                      | 2.1               | -                | V    |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | $V_{GS} = -10 \text{ V}, \text{ I}_{D} = -10.5 \text{ A}$                     | 0.011             | 0.011            | Ω    |
|                                                                        |                     | $V_{GS}$ = - 4.5 V, I <sub>D</sub> = - 10.5 A                                 | 0.018             | 0.017            |      |
| Forward Transconductance <sup>a</sup>                                  | <b>g</b> fs         | $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -10.5 \text{ A}$                     | 18                | 26               | S    |
| Dynamic <sup>b</sup>                                                   |                     |                                                                               |                   |                  |      |
| Input Capacitance                                                      | C <sub>iss</sub>    | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz                    | 3400              | 3435             | pF   |
| Output Capacitance                                                     | C <sub>oss</sub>    |                                                                               | 456               | 450              |      |
| Reverse Transfer Capacitance                                           | C <sub>rss</sub>    |                                                                               | 357               | 280              |      |
| Total Gate Charge                                                      | Qg                  | V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10.5 A | 70                | 74               | nC   |
| Gate-Source Charge                                                     | Q <sub>gs</sub>     |                                                                               | 11                | 11               |      |
| Gate-Drain Charge                                                      | Q <sub>gd</sub>     |                                                                               | 16                | 16               |      |

Note

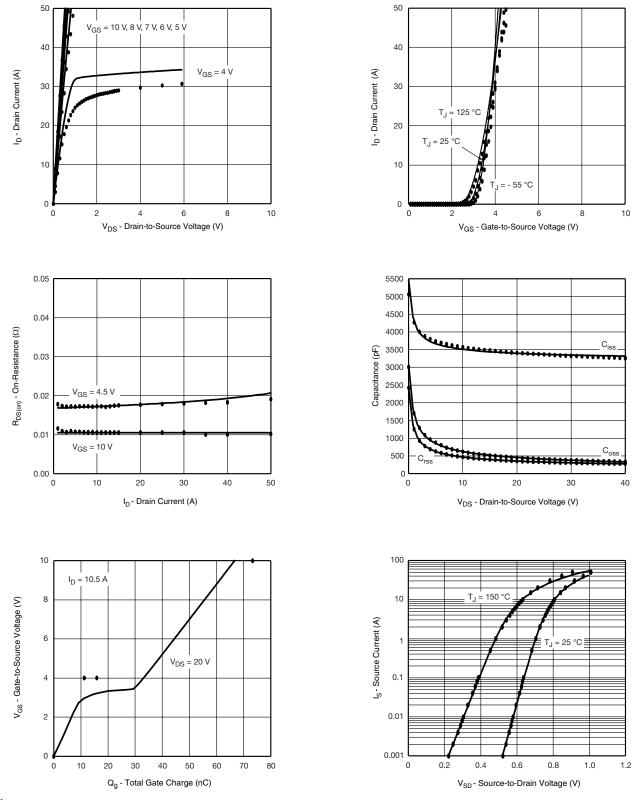
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.



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## COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)



#### Note

• Dots and squares represent measured data.

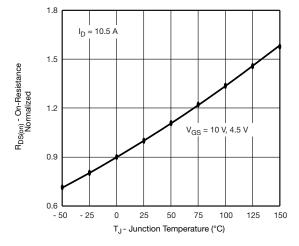
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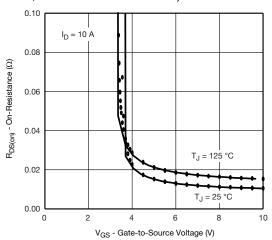
Document Number: 65995



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## COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)





Note

• Dots and squares represent measured data.

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